TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

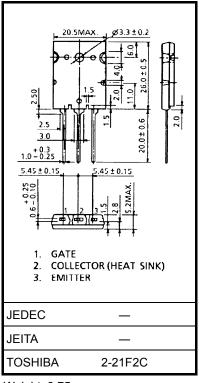
GT50J121

High Power Switching Applications Fast Switching Applications

- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS): Operating frequency up to 50 kHz (reference)
 - High speed: $t_f = 0.05 \ \mu s$ (typ.)
 - Low switching loss: E_{on} = 1.30 mJ (typ.) : E_{off} = 1.34 mJ (typ.)
- Low saturation Voltage: V_{CE} (sat) = 2.0 V (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	Ι _C	50	A	
	1 ms	I _{CP}	100		
Collector power dissipation (Tc = 25°C)		P _C	240	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 9.75 g

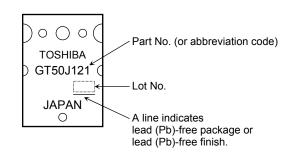
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance	R _{th (j-c)}	0.521	°C/W

Marking

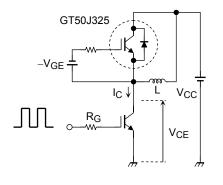


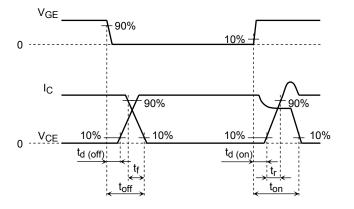
Unit: mm

Electrical Characteristics (Ta = 25°C)

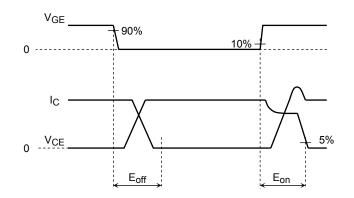
Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	$V_{GE}=\pm 20~V,~V_{CE}=0$	_		±500	nA
Collector cut-off current		ICES	$V_{CE} = 600 \text{ V}, \text{ V}_{GE} = 0$	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (OFF)}	$I_C=5\ mA,\ V_{CE}=5\ V$	3.5	_	6.5	V
Collector-emitter saturation voltage		V _{CE (sat)}	$I_C = 50$ A, $V_{GE} = 15$ V	_	2.0	2.45	V
Input capacitance		Cies	$V_{CE}=10~V,~V_{GE}=0,~f=1~MHz$	_	7900	—	pF
Switching time	Turn-on delay time	t _{d (on)}	Inductive load $V_{CC}=300 \text{ V, } I_C=50 \text{ A}$ $V_{GG}=+15 \text{ V, } R_G=13 \Omega \tag{Note 1}$ (Note 1) (Note 2)		0.09	_	μs
	Rise time	tr			0.07	_	
	Turn-on time	t _{on}			0.24	_	
	Turn-off delay time	^t d (off)			0.30	_	
	Fall time	t _f		_	0.05	_	
	Turn-off time	t _{off}		_	0.43	_	
Switching loss	Turn-on switching loss	Eon		_	1.30	_	mJ
	Turn-off switching loss	E _{off}			1.34		

Note 1: Switching time measurement circuit and input/output waveforms

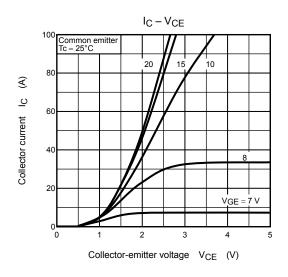


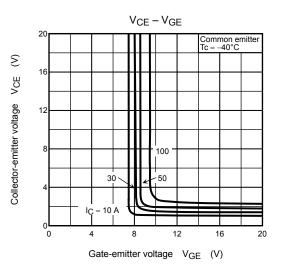


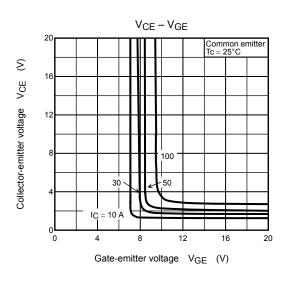
Note 2: Switching loss measurement waveforms

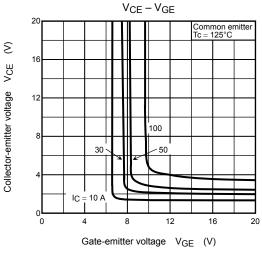


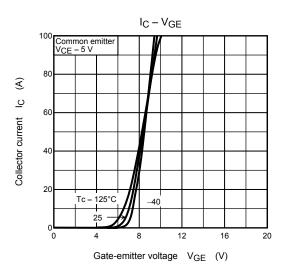
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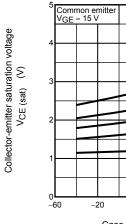


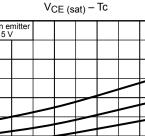


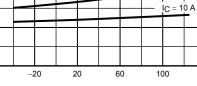




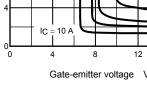












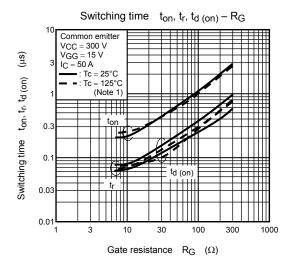
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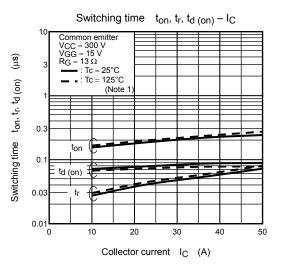
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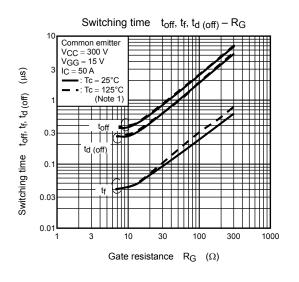
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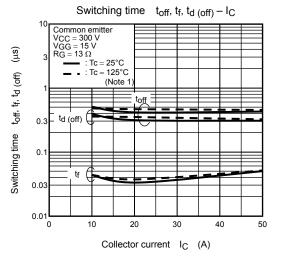
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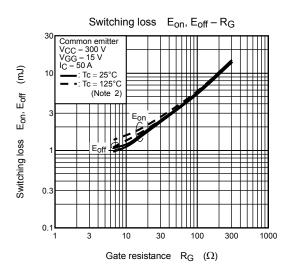
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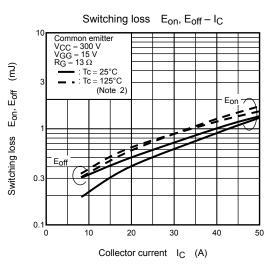




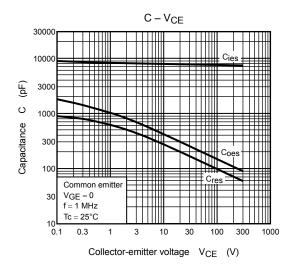


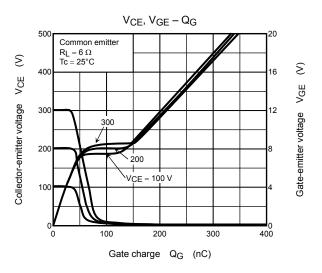


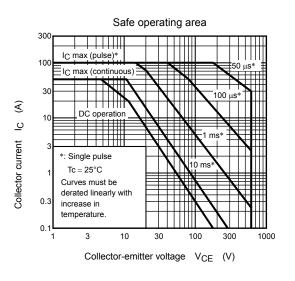


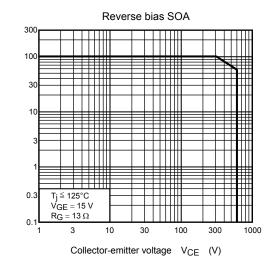


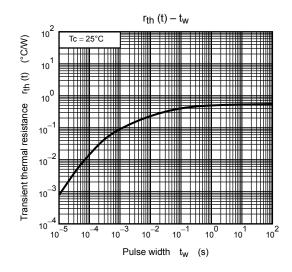
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Collector current

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